Supplementary information

Properties and growth of large single crystal of one dimensional organic lead iodine perovskites

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Experimental

Synthesis

0.5 mmol Benzylamine and 1 mmol PbI₂ were mixed in 10ml DMF. Then 5ml hydroiodic acid (57% wt) was dropped to the solution. 2 ml 50% phosphorous acid solution was added to stabilize hydroiodic acid. A clear yellow solution was formed finally. Large single crystals of DMAPbI₃ were acquired by evaporation of the solution at room temperature for about two weeks.

Measurement Section.

The elemental analysis was recorded on a Heraeus CHN-0-Rapid elemental analyser. The absorption spectrum was measured by a PV Measurements Model QEX10 through using Integral Sphere Method from 300nm to 1100nm. The single crystal X-ray diffraction was measured by a Bruker D8 QUEST. Powder X-ray diffraction (PXRD) was measured on a Rigaku D/MAX 2000 PC X-ray diffractometer. DSC measurements of single crystals were recorded by using a NETZSCH DSC 200F3 in the temperature range of 100–300 K. The complex permittivity was measured using a Tonghui TH2828A LCR meter. The photoluminescence spectra were detected by time resolved fluorescence spectra (FLSP20, Edinburgh, Ihstrcamenss). The absorption spectra were measured by Quantum efficiency tester. Raman spectra were collected using a Horiba Jobin Yvon HR800 spectrometer device by means of a 488 nm laser line. P–E hysteresis loops were recorded on a Precision Premier II (Radiant Technologies, Inc.) using Sawyer-Tower Circuit.

Elemental analysis: To ascertain the structure and purity of compounds DMAPbI₃,we quantitatively measured the mass fractions of carbon, and nitrogen in the compound by means of CHN elemental analysis. The results are C 3.91%, N 2.11% for the compound, which are coincident with the theoretical values (C 3.79, N 2.21%). The measurement error of the mass fractions is about 0.3%.

Option	Space Group	No. T	ype	Axes	CS	D R(syn	n) N(eq) Sys	t. Abs	. CFOM
[A]	P-31c	#163	centro	1	23	0.075	1490	0.8 /	5.6	10.32
[B]	P31c	#159	non-cen	1	12	0.075	1490	0.8 /	5.6	14.73
[C]	P6(3)mc	#186	non-cen	1	21	0.080	1665	0.8 /	5.6	12.77
[D]	P6(3)/mmc	#194	centro	1	16	0.080	1665	0.8 /	5.6	13.22
[E]	P-62c	#190	non-cen	1	11	0.080	1665	0.8 /	5.6	16.56

Table S1. Xprep information of the DMAPbI₃ single crystal XRD data measured at room temperature.

 Table S2 Crystallographic data

Temperature	100 K	293 K				
Formula	C ₂ NH ₈ PbI ₃	C ₂ NH ₈ PbI ₃				
Formula weight	633.98	633.98				
Crystal system	monoclinic	hexagonal				
Space group	$P2_1$	P6 ₃ /mmc				
<i>a</i> / Å	8.9303(6)	8.7799(12)				
<i>b</i> / Å	14.6910(9)	8.7799(12)				
<i>c</i> / Å	7.9790(5)	8.193(2)				
lpha / °	90	90				
β / °	95.994(4)	90				
γ/°	90	120				
$V/\text{\AA}^3$	1041.08(11)	546.94(19)				
Ζ	4	2				
$D_{\rm c}$ / g·cm ⁻³	4.045	3.850				
<i>F</i> (000)	1072	520				
GOF on F^2	1.035	1.200				
$R1, wR2 [I > 2\sigma(I)]$	0.0716, 0.1781	0.0413, 0.0946				
R1,wR2 (all data)	0.0966, 0.1925	0.0573, 0.1002				
Flack parameter	0.470(18)	None				



Fig. S1 Microscope photo of 1D $DMAPbI_3$ single crystals with regular shape at the beginning of the growth.



Fig. S2 Microscope photo of 1D DMAPbI $_3$ single crystals with irregular shape.



Fig. S3 XRD of the largest area face of single crystal DMAPbI₃ at room temperature.



Fig. S4 PE loop measured at different temperature with 50 Hz frequency.



Fig. S5 Raman spectra of DMAPbI₃ measured at room temperature.



Fig. S6 Pyroelectric current and the corresponding spontaneous polarization of DMAPbl₃ measured after positive polarization and negative polarization with 10 K/min heating speed.



Fig. S7 The temperature dependent dielectric loss in the heating process and the cooling process.



Fig. S8 The temperature dependent dielectric loss measured with 1000 kHz in the heating process and the cooling process